

FY8AAJ-03F

High-Speed Switching Use
Nch Power MOS FET

REJ03G0280-0100

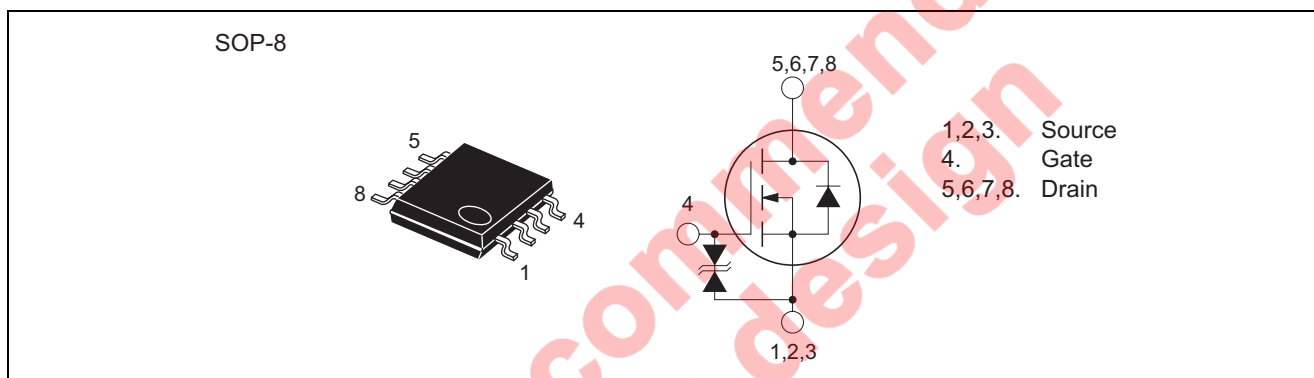
Rev.1.00

Aug.20.2004

Features

- Drive voltage : 4 V
- V_{DSS} : 30 V
- $r_{DS(ON) (max)}$: 28 m Ω
- I_D : 8 A

Outline



Applications

Motor control, lamp control, solenoid control, DC-DC converters, etc.

Maximum Ratings

($T_c = 25^\circ\text{C}$)

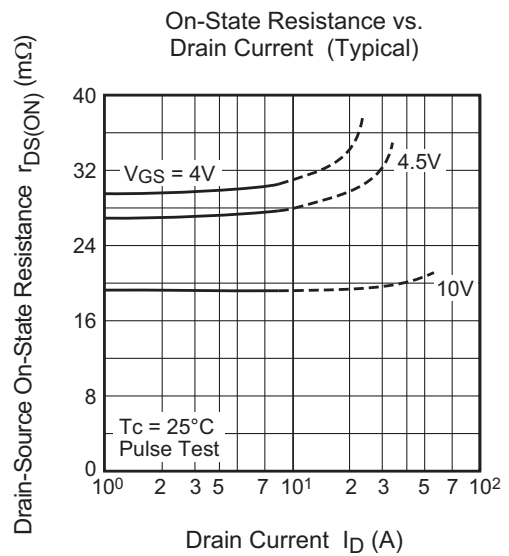
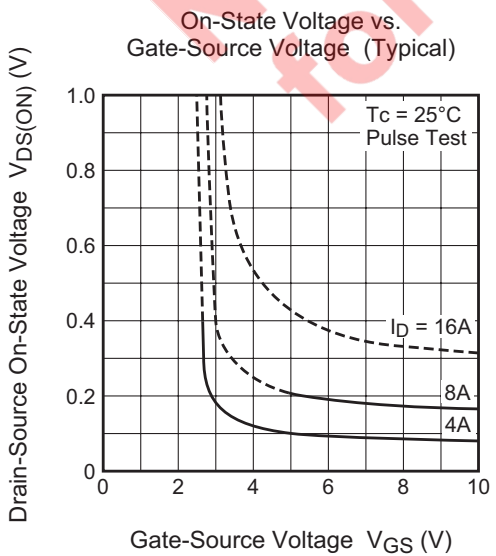
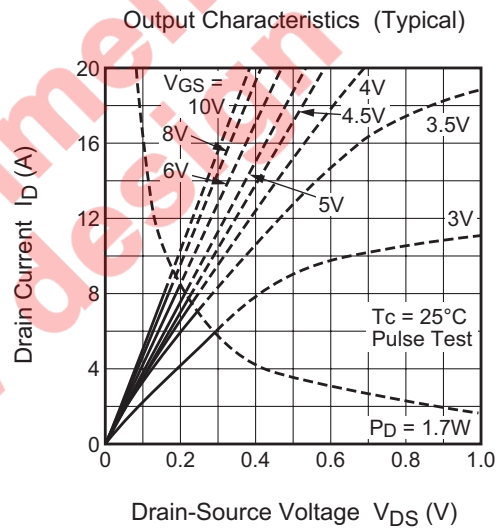
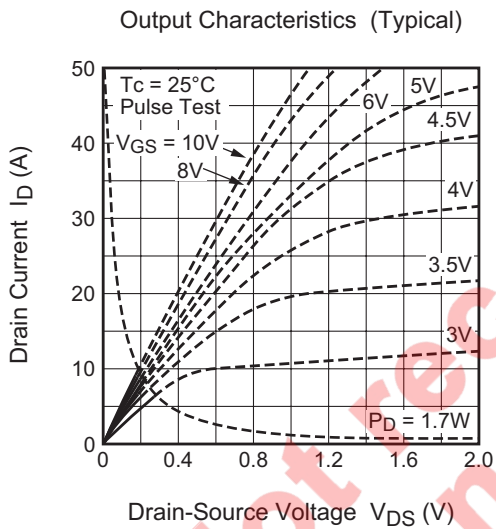
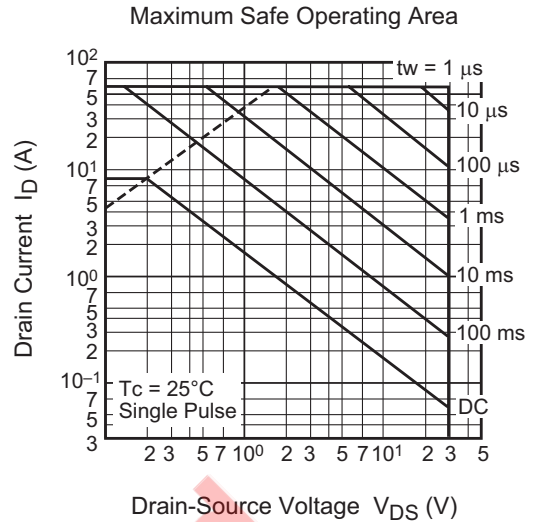
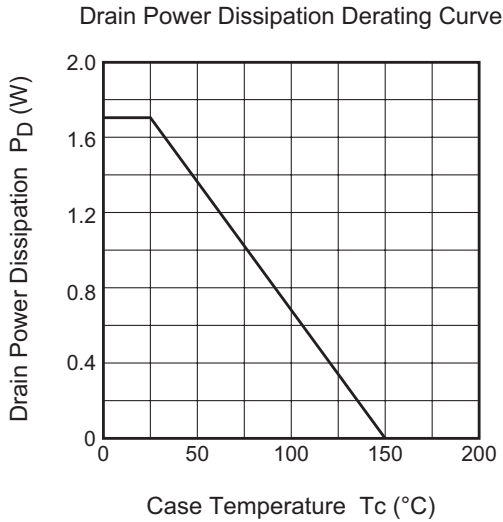
Parameter	Symbol	Ratings	Unit	Conditions
Drain-source voltage	V_{DSS}	30	V	$V_{GS} = 0\text{ V}$
Gate-source voltage	V_{GSS}	± 20	V	$V_{DS} = 0\text{ V}$
Drain current	I_D	8	A	
Drain current (Pulsed)	I_{DM}	56	A	
Avalanche current (Pulsed)	I_{DA}	8	A	$L = 10\ \mu\text{H}$
Source current	I_S	1.5	A	
Source current (Pulsed)	I_{SM}	6.0	A	
Maximum power dissipation	P_D	1.7	W	
Channel temperature	T_{ch}	- 55 to +150	$^\circ\text{C}$	
Storage temperature	T_{stg}	- 55 to +150	$^\circ\text{C}$	
Mass	—	0.07	g	Typical value

Electrical Characteristics

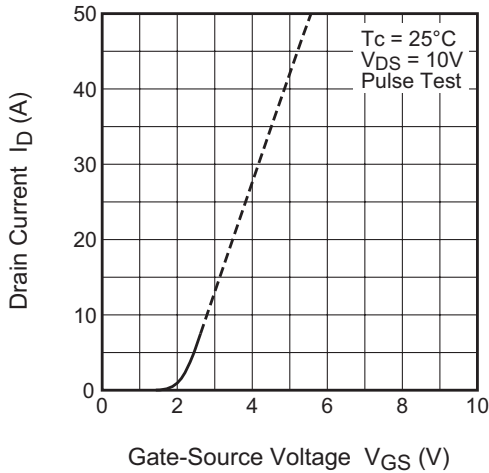
(Tch = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Drain-source breakdown voltage	$V_{(BR)DSS}$	30	—	—	V	$I_D = 1 \text{ mA}$, $V_{GS} = 0 \text{ V}$
Gate-source breakdown voltage	$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}$, $V_{DS} = 0 \text{ V}$
Drain-source leakage current	I_{DSS}	—	—	0.1	mA	$V_{DS} = 30 \text{ V}$, $V_{GS} = 0 \text{ V}$
Gate-source leakage current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0 \text{ V}$
Gate-source threshold voltage	$V_{GS(th)}$	1.0	1.5	2.0	V	$I_D = 1 \text{ mA}$, $V_{DS} = 10 \text{ V}$
Drain-source on-state resistance	$r_{DS(ON)}$	—	22	28	m Ω	$I_D = 8 \text{ A}$, $V_{GS} = 10 \text{ V}$
Drain-source on-state resistance	$r_{DS(ON)}$	—	31	43	m Ω	$I_D = 4 \text{ A}$, $V_{GS} = 4.5 \text{ V}$
Drain-source on-state resistance	$r_{DS(ON)}$	—	35	50	m Ω	$I_D = 4 \text{ A}$, $V_{GS} = 4 \text{ V}$
Drain-source on-state voltage	$V_{DS(ON)}$	—	0.176	0.224	V	$I_D = 8 \text{ A}$, $V_{GS} = 10 \text{ V}$
Forward transfer admittance	$ y_{fs} $	—	13	—	S	$I_D = 8 \text{ A}$, $V_{DS} = 10 \text{ V}$
Input capacitance	C_{iss}	—	600	—	pF	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$
Output capacitance	C_{oss}	—	200	—	pF	
Reverse transfer capacitance	C_{rss}	—	90	—	pF	
Turn-on delay time	$t_{d(on)}$	—	10	—	ns	$V_{DD} = 15 \text{ V}$, $I_D = 4 \text{ A}$, $V_{GS} = 10 \text{ V}$, $R_G = 5 \text{ }\Omega$
Rise time	t_r	—	15	—	ns	
Turn-off delay time	$t_{d(off)}$	—	40	—	ns	
Fall time	t_f	—	6.5	—	ns	
Total gate charge	Q_g	—	13.8	—	nC	$V_{DD} = 15 \text{ V}$, $I_D = 8 \text{ A}$, $V_{GS} = 10 \text{ V}$
Gate-source charge	Q_{gs}	—	1.6	—	nC	
Gate-drain charge	Q_{gd}	—	3.5	—	nC	
Source-drain voltage	V_{SD}	—	0.75	1.10	V	$I_S = 1.5 \text{ A}$, $V_{GS} = 0 \text{ V}$
Thermal resistance	$R_{th(ch-a)}$	—	—	73.5	$^{\circ}\text{C/W}$	Channel to air
Reverse recovery time	t_{rr}	—	40	—	ns	$I_S = 1.5 \text{ A}$, $dis/dt = -50 \text{ A}/\mu\text{s}$

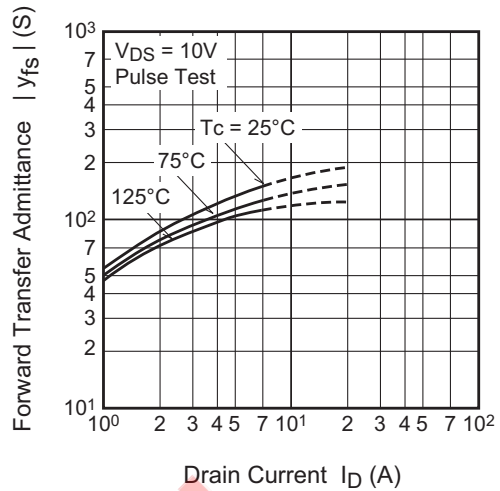
Performance Curves



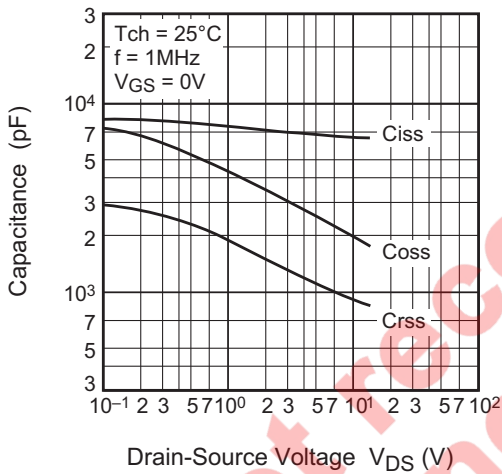
Transfer Characteristics (Typical)



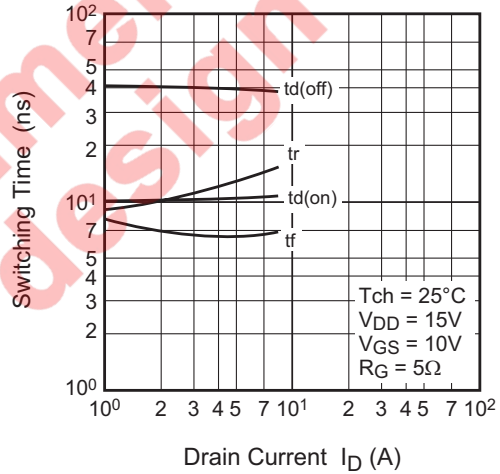
Forward Transfer Admittance vs. Drain Current (Typical)



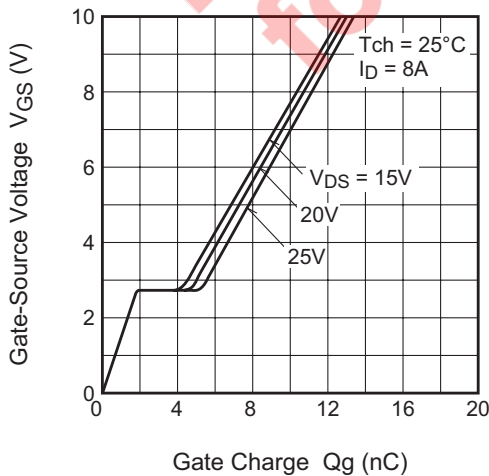
Capacitance vs. Drain-Source Voltage (Typical)



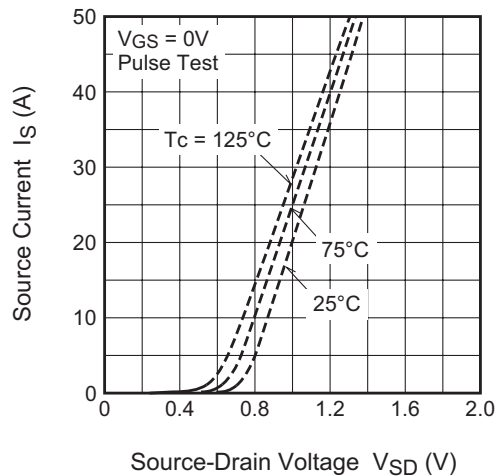
Switching Characteristics (Typical)

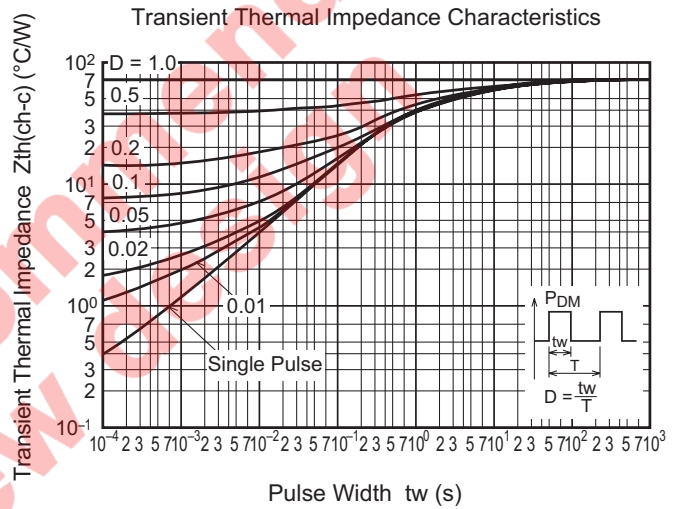
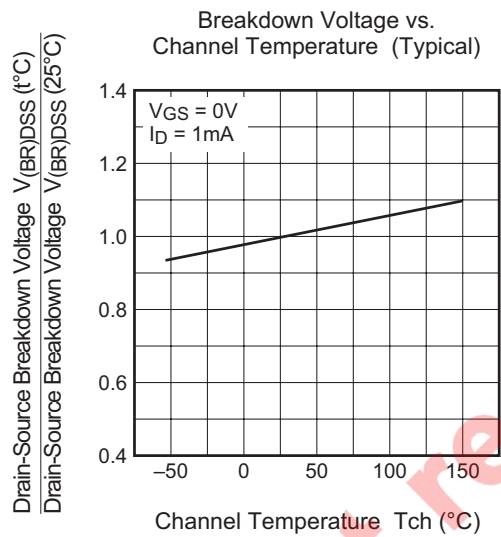
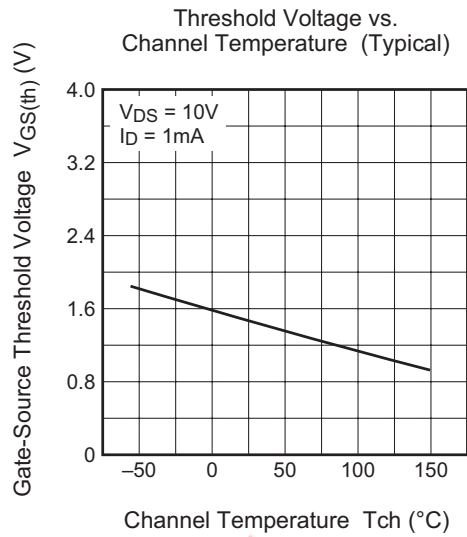
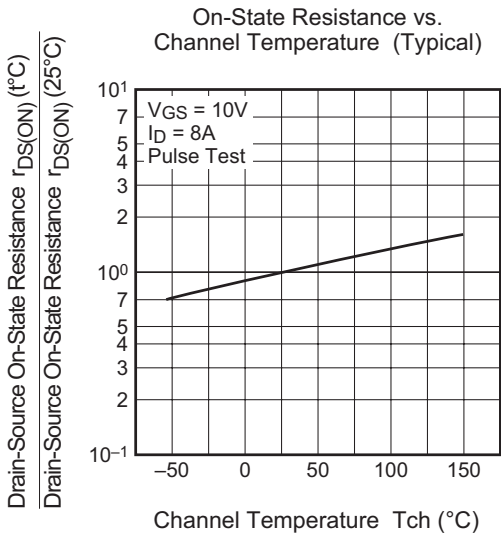


Gate-Source Voltage vs. Gate Charge (Typical)

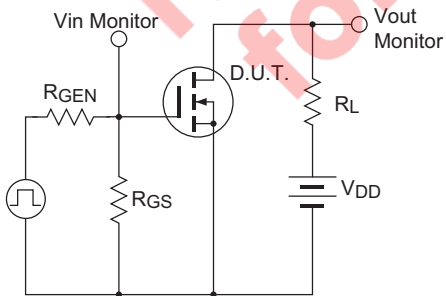


Source-Drain Diode Forward Characteristics (Typical)

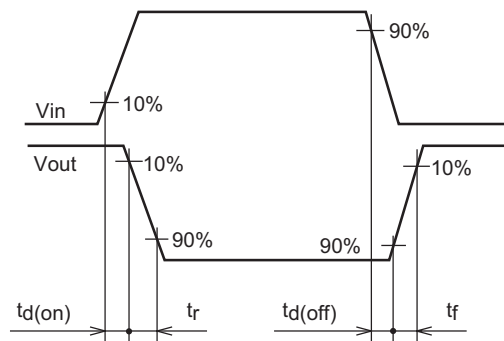




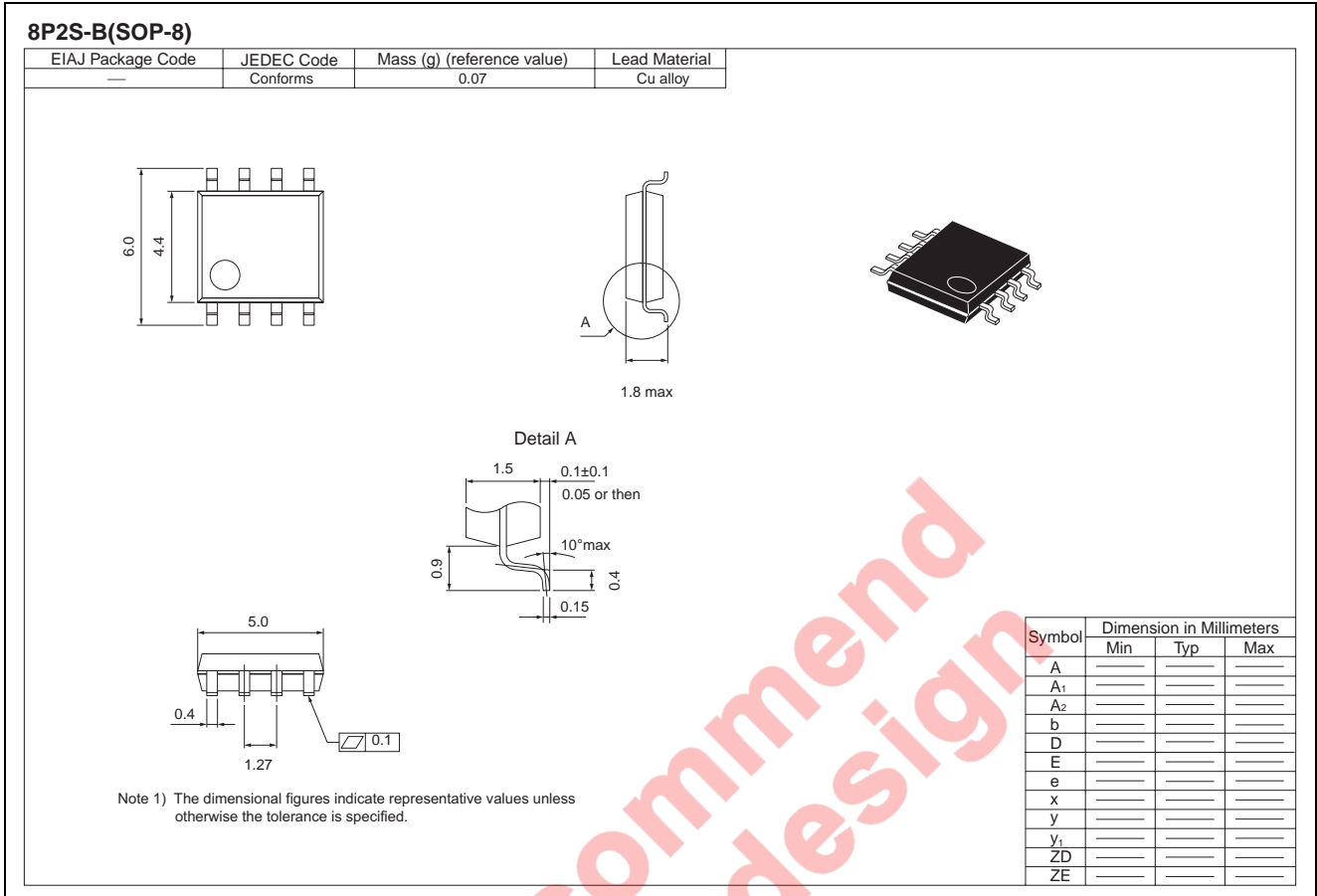
Switching Time Measurement Circuit



Switching Waveform



Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Surface-mounted type	Taping	3000	Type name – T +Direction (1 or 2) +3	FY8AAJ-03F-T13
Surface-mounted type	Plastic Magazine (Tube)	100	Type name	FY8AAJ-03F

Note : Please confirm the specification about the shipping in detail.

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